TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC74AP,TC74HC74AF,TC74HC74AFN

Dual D-Type Flip Flop Preset and Clear

The TC74HC74A is a high speed CMOS D FLIP FLOP fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

The signal level applied to the D INPUT is transferred to Q OUTPUT during the positive going transition of the CLOCK pulse.

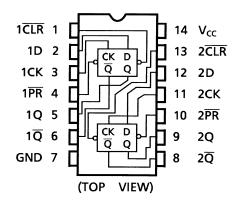
CLEAR and PRESET are independent of the CLOCK and are accomplished by setting the appropriate input to an "L" level.

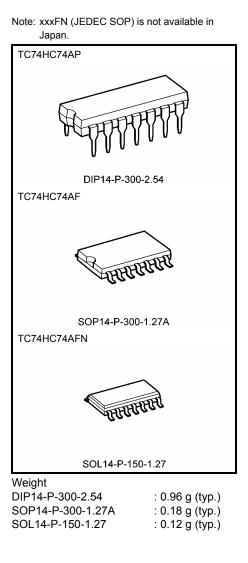
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High speed: $f_{max} = 77 \text{ MHz}$ (typ.) at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 2 \mu A (max)$ at $Ta = 25^{\circ}C$
- High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: |IOH| = IOL = 4 mA (min)
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: VCC (opr) = 2~6 V
- Pin and function compatible with 74LS74

Pin Assignment





<u>TOSHIBA</u>

IEC Logic Symbol

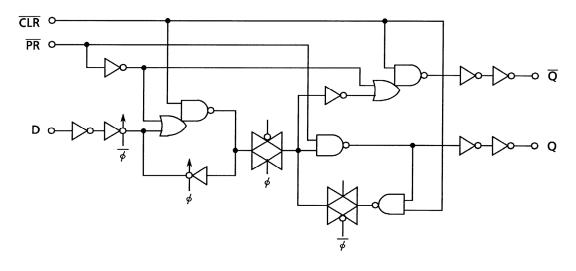
1PR	(4) N	S	(5)
1CK	(3)	> C1	<u> </u>
1D	(2) (1)	1D	(6) 1Q
1CLR		R	
2 <mark>PR</mark> 2CK	(10)		(9)
2CK	(11)		(3) 2Q
2D	(12)		(8) 77
2CLR	(13)		<u>(0)</u> 2Q

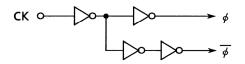
Truth Table

	Inp	uts		Outputs		Function
CLR	PR	D	СК	Q	Q	Function
L	Н	Х	Х	L	Н	Clear
Н	L	Х	Х	Н	L	Preset
L	L	Х	Х	Н	Н	_
Н	Н	L		L	Н	—
Н	Н	Н		Н	L	_
Н	Н	Х		Qn	\overline{Q}_{n}	No Change

X: Don't care

System Diagram





Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7	V
DC input voltage	V _{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC output voltage	V _{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input diode current	I _{IK}	±20	mA
Output diode current	I _{OK}	±20	mA
DC output current	I _{OUT}	±25	mA
DC V _{CC} /ground current	ICC	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65° C. From Ta = 65 to 85° C a derating factor of -10 mW/°C shall be applied until 300 mW.

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2~6	V
Input voltage	V _{IN}	0~V _{CC}	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
		0~1000 (V _{CC} = 2.0 V)	
Input rise and fall time	t _r , t _f	0~500 (V _{CC} = 4.5 V)	ns
		0~400 (V _{CC} = 6.0 V)	

Operating Ranges (Note)

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

			Test Condition		-	Ta = 25°0)	Ta = −40~85°C			
Characteristics	Symbol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit	
				2.0	1.50	_	_	1.50	_		
High-level input voltage	VIH		_	4.5	3.15	—	—	3.15	—	V	
Ŭ				6.0	4.20		_	4.20	—		
				2.0	—		0.50	—	0.50		
Low-level input voltage	VIL		—	4.5	—		1.35	—	1.35	V	
Ŭ				6.0	—		1.80	—	1.80		
	V _{OH}	VIN = VIH or VIL	I _{OH} = -20 μA	2.0	1.9	2.0		1.9	—		
				4.5	4.4	4.5	_	4.4	—		
High-level output voltage				6.0	5.9	6.0		5.9	—	V	
Ũ			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	_	
			$I_{OH} = -5.2 \text{ mA}$	6.0	5.68	5.80		5.63	—		
		VIN		2.0	_	0.0	0.1	_	0.1		
			$I_{OL}=20~\mu A$	4.5	—	0.0	0.1	—	0.1		
Low-level output voltage	V _{OL}	= V _{IH} or		6.0	—	0.0	0.1	—	0.1	V	
Ũ		VIL	$I_{OL} = 4 \text{ mA}$	4.5	_	0.17	0.26	_	0.33		
			$I_{OL} = 5.2 \text{ mA}$	6.0	_	0.18	0.26	—	0.33		
Input leakage current	I _{IN}	$V_{IN} = V_{CC}$ or GND		6.0	_	_	±0.1	_	±1.0	μA	
Quiescent supply current	Icc	$V_{IN} = V_C$	_C or GND	6.0	_	_	2.0		20.0	μA	

Timing Requirements (input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol	Test Condition	Test Condition			Ta = _40 ∼85°C	Unit
			V _{CC} (V)	Тур.	Limit	Limit	
Minimum pulse width	t		2.0	_	75	95	
(CK)	t _{W (L)}	—	4.5	—	15	19	ns
(CK)	tw (H)		6.0	_	13	16	
Minimum pulse width			2.0		75	95	
$(\overline{\text{CLR}}, \overline{\text{PR}})$	t _{W (L)}	—	4.5	—	15	19	ns
(ULK, FK)			6.0	_	13	16	
			2.0		75	95	
Minimum set-up time	t _s	—	4.5	—	15	19	ns
			6.0	_	13	16	
			2.0	—	0	0	
Minimum hold time	th	—	4.5	—	0	0	ns
			6.0	_	0	0	
Minimum removal time			2.0		25	30	
$(\overline{\text{CLR}}, \overline{\text{PR}})$	t _{rem}	—	4.5	—	5	6	ns
(CLR, PR)			6.0	_	4	5	
			2.0	—	6	5	
Clock frequency	f	—	4.5	—	31	25	MHz
			6.0	_	36	29	

AC Characteristics (C_L = 15 pF, V_{CC} = 5 V, Ta = 25°C, input: $t_r = t_f = 6$ ns)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Output transition time	tтLH tтHL	_	_	6	12	ns
Propagation delay time (CK-Q, \overline{Q})	t _{pLH} t _{pHL}	_	_	13	26	ns
Propagation delay time $(\overline{\text{CLR}}, \overline{\text{PR}} - Q, \overline{Q})$	t _{pLH} t _{pHL}	_	_	14	26	ns
Maximum clock frequency	f _{max}	_	36	77	—	MHz

AC Characteristics ($C_L = 50 \text{ pF}$, input: $t_r = t_f = 6 \text{ ns}$)

		Test Condition		-	Га = 25°С)	Ta = -4		
Characteristics	acteristics Symbol		V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit
Output transition time	tт∟н tтн∟	_	2.0 4.5 6.0		30 8 7	75 15 13		95 19 16	ns
Propagation delay time $(CK-Q, \overline{Q})$	^t pLH ^t pHL	_	2.0 4.5 6.0		48 16 13	150 30 26		190 38 32	ns
Propagation delay time $(\overline{\text{CLR}}, \overline{\text{PR}} - \text{Q}, \overline{\text{Q}})$	t _{pLH} t _{pHL}	_	2.0 4.5 6.0		51 17 15	150 30 26		190 38 32	ns
Maximum clock frequency	f _{max}	_	2.0 4.5 6.0	6 31 36	21 63 67		5 25 29		MHz
Input capacitance	C _{IN}	—	•	_	5	10		10	pF
Power dissipation capacitance	C _{PD}		(Note)	_	34	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

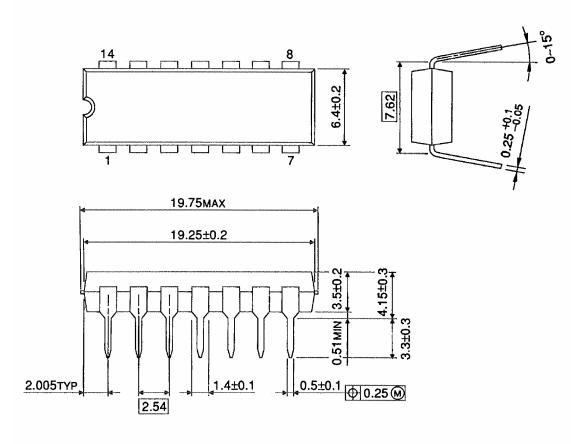
 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$ (per F/F)

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Package Dimensions

DIP14-P-300-2.54

Unit : mm



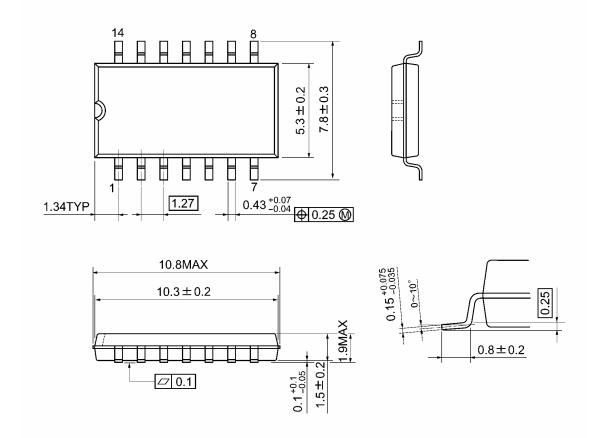
Weight: 0.96 g (typ.)

TOSHIBA

Package Dimensions

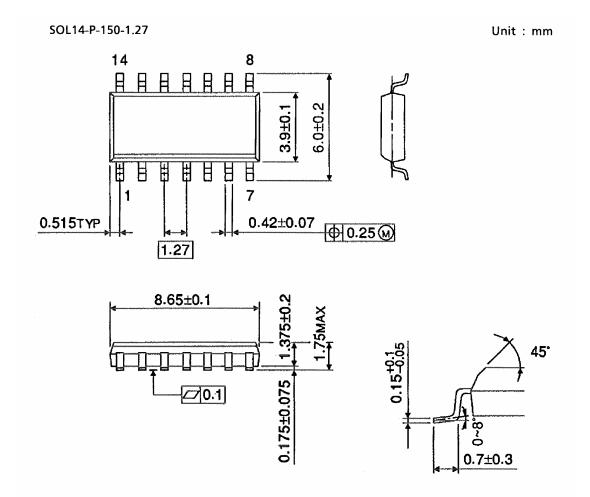
SOP14-P-300-1.27A

Unit: mm



Weight: 0.18 g (typ.)

Package Dimensions (Note)



Note: This package is not available in Japan.

Weight: 0.12 g (typ.)

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20070701-EN GENERAL

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